

Notice of References Cited	Application/Control No. 10/849,589	Applicant(s)/Patent Under Reexamination SAXLER, ADAM WILLIAM	
	Examiner John C. Ingham	Art Unit 2814	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-2005/0006663	01-2005	Howard et al.	257/134
	B	US-6,500,257	12-2002	Wang et al.	117/95
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Linthicum, Kevin, et al. Pendoeepitaxy of gallium nitride thin films, 12 July 1999, Applied Physics Letters, Vol 75 Num 2, p196-198
	V	Follstaedt, D.M., et al. Minimizing threading dislocations by redirection during cantilever epitaxial growth of GaN, 7 October 2002, Applied Physics Letters, Vol 81 Num 15, p2758-2760
	W	Kidoguchi, Isao, et al. Air-bridged lateral epitaxial overgrowth of GaN thin films, 19 June 2000, Applied Physics Letters, Vol 76 Num 25, p3768-3770
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.